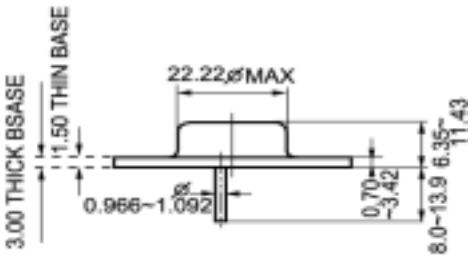
2SC1580

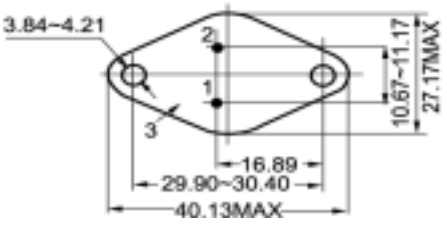
Silicon NPN Transistors

◆ Features

1B 2E 3C

• With TO-3 package





TO-3

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{CB}	Collector to base voltage	600	V
V_{CEO}	Collector to emitter voltage	500	V
V_{CER}	Emitter to base voltage		
V_{EB}	Emitter to base voltage	5.0	V
I_B	Base Current		
I_C	Collector current-Continuous	15	A
P_D	Total Power Dissipation@TC=25℃	150	W
T_j	Junction temperature	200	℃
T_{stg}	Storage temperature	-65~200	℃

Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{CEO}	Collector-Emitter Sustaining Voltage	I_C=5mA; I_B=0	500		V
V_{CER}	Collector-Emitter Sustaining Voltage				
I_{CEO}	Collector Cutoff Current	V_{CE}=500V; I_B=0		0.5	mA
I_{CEX}	Collector Cutoff Current				
I_{CBO}	Collector-emitter breakdown voltage	Vcb=600V I_E=0		0.1	mA
V_{EBO}	Emitter Cutoff Current				
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	I_C=6.0A; I_B=1A		5.0	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages				
$V_{CE(sat-3)}$	Collector-emitter saturation voltages				
$V_{CE(sat-4)}$	Collector-emitter saturation voltages				
h_{FE-1}	Forward current transfer ratio	I_C=4A; V_{CE}=5V	20		
h_{FE-2}	Forward current transfer ratio				
$V_{BE(on)}$	Base-emitter On voltages				
f_T	Current Gain-Bandwidth Product				
h_{fe}	Small-Signal Current Gain				
f_{hfe}	Small-Signal Current Gain Cutoff Frequency				